鼎德丰
DING DE FENG

PNP Silicon Transistor

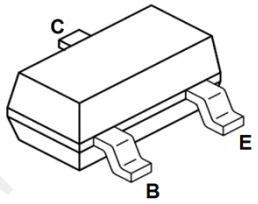
MMBTA92

Package: SOT-23

Complement to MMBTA42

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	-300	V
Collector-emitter voltage	BV_{CEO}	-300	V
Emitter-base voltage	BV_{EBO}	-6	V
Collector current	I_{CM}	-500	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃



SOT-23

Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-100μA, I_E=0	-300			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-1mA, I_B=0	-300			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-100μA, I_C=0	-6			V
collector-base cut-off current	I_{CBO}	V_{CB}=-200V, I_E=0			-0.1	μA
collector-emitter cut-off current	I_{CEO}	V_{CE}=-200V, I_B=0			-0.1	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-0.1	μA
DC current gain	H_{FE1}	V_{CE}=-10V, I_B=-1mA	25			
	H_{FE2}	V_{CE}=-10V, I_B=-10mA	40		240	
	H_{FE3}	V_{CE}=-10V, I_B=-30mA	40			
collector-emitter saturation voltage	$V_{CE(SAT)}$	I_C=-20mA, I_B=-2mA			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C=-20mA, I_B=-2mA			-0.9	V
Transition frequency	f_T	V_{CE}=-20V, I_B=-10mA, f = 100 MHz	50			MHz